

Silicon NPN Power Transistors

KSD2058

DESCRIPTION

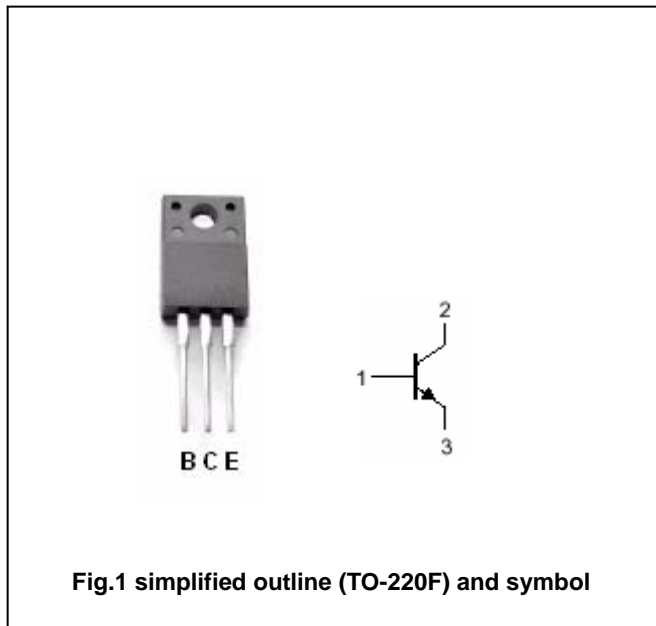
- With TO-220F package
- Complement to type KSB1366

APPLICATIONS

- With general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _{CBO}	Collector-base voltage	Open emitter	60	V
V _{CEO}	Collector-emitter voltage	Open base	60	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		3	A
I _B	Base current		0.5	A
P _C	Collector dissipation	T _a =25	1.5	W
		T _C =25	25	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A ; I _B =0.2A			1.5	V
V _{BE}	Base-emitter on voltage	I _C =0.5A ; V _{CE} =5V		3.0		V
I _{CBO}	Collector cut-off current	V _{CB} =60V ; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =7V ; I _C =0			1	mA
h _{FE}	DC current gain	I _C =0.5A ; V _{CE} =5V	60		300	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =5V		3.0		MHz
C _{OB}	Collector output capacitance	f=1MHz ; V _{CB} =10V		35		pF

Switching times

t _{on}	Turn-on time	I _C =2.0A I _{B1} =-I _{B2} =0.2A V _{CC} =30V , R _L =15		0.65		μs
t _s	Storage time			1.3		μs
t _f	Fall time			0.65		μs

◆ h_{FE} Classifications

O	Y	G
60-120	100-200	150-300

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PACKAGE OUTLINE

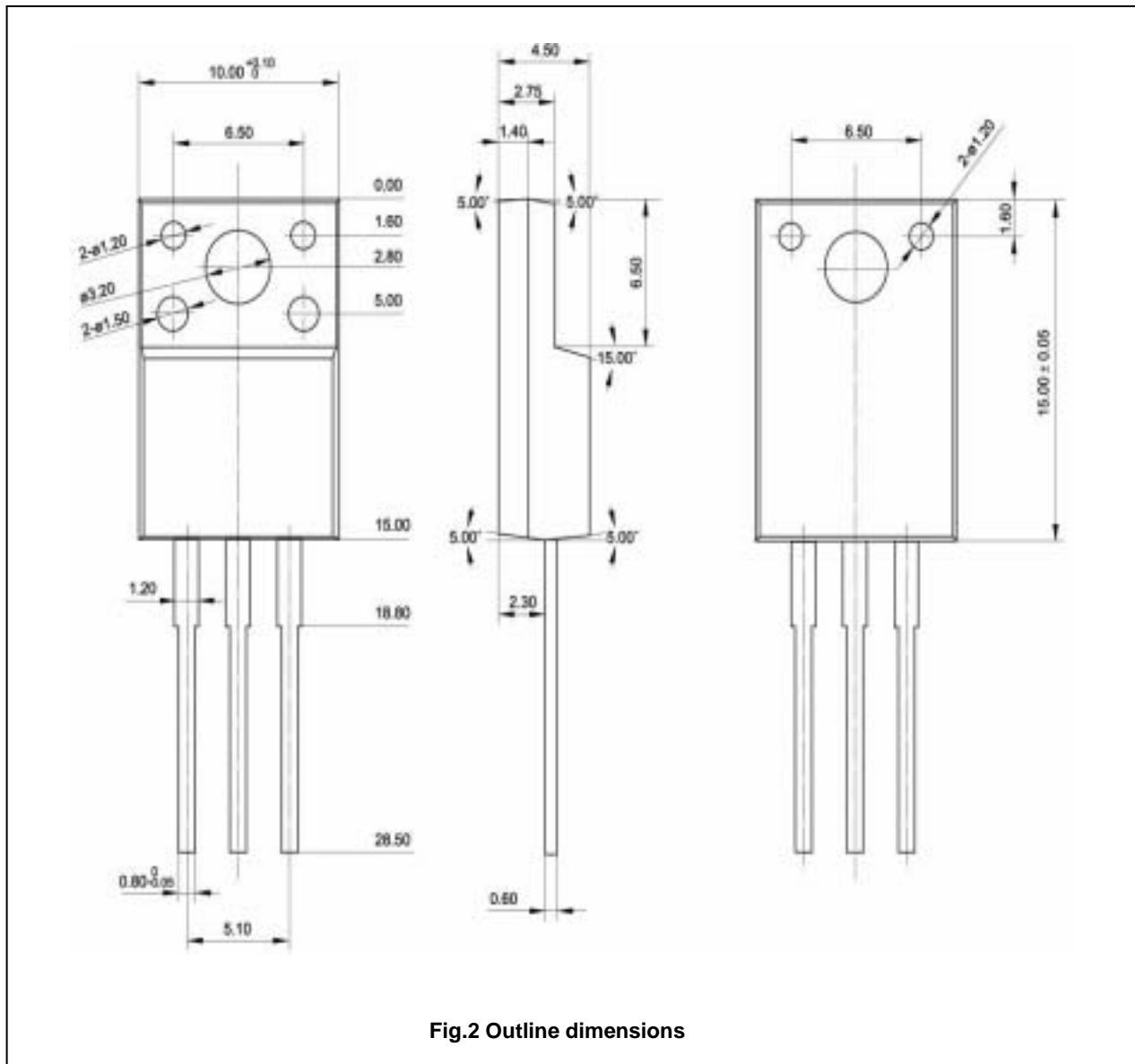


Fig.2 Outline dimensions